

SPEC SHEET (FOR REFERENCE)	SHEET No.	Rev.	Page.
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TYPE : 6PT2006N3T**

CHIP SIZE	0.23 * 0.23 mm
WAFER SIZE	6 inch
POSSIBLE DIE PER WAFER	290,000 pcs

Maximum Ratings(Ta=25°C)

Characteristics	Symbol	Ratings	Unit
Drain-source voltage	VDSS	60	V
Gate-source voltage	VGSS	±20	V
Drain Current (DC)	ID	0.05	A

* For Reference

WAFER PROBING SPEC (Ta=25°C)

No	MODE	LIMIT				CONDITIONS
		MIN.	Typ	MAX.	UNIT	
1	IGSS			±5	uA	VGS= ±20V VDS= 0V
2	IDSS			500	nA	VDS= 60V VGS= 0V
3	BVDSS	63			V	ID= 1mA
4	VTH	1		2.4	V	VDS=10V IDS=100uA
5	Ron 1		5.5	7.5	Ω	ID=50mA VGS=10V
6	Ron 2		8	10.5	Ω	ID=30mA VGS=4.0V
7	VSD			1.2	V	IS=100mA

※ Built-in ZD between Gate and Source

TENTATIVE

NOTE: